

60V N-Channel MOSFET

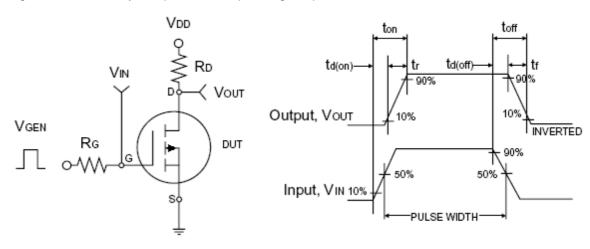


Electrical Specifications (Ta = 25°C, unless otherwise noted)

Parameter	Conditions	Symbol	Min	Тур	Max	Unit		
Static								
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 10\mu A$	BV _{DSS}	60			V		
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	$V_{GS(TH)}$	1.0		2.5	V		
Gate Body Leakage	$V_{GS} = \pm 20V, V_{DS} = 0V$	I _{GSS}			±10	uA		
Zero Gate Voltage Drain Current	$V_{DS} = 60V, V_{GS} = 0V$	I _{DSS}			1.0	uA		
Davis Co. and Co. Otata Basista	$V_{GS} = 10V, I_D = 100mA$	D		3	5	Ω		
Drain-Source On-State Resistance	$V_{GS} = 5V, I_D = 100mA$	$R_{DS(ON)}$		3.6	5.5			
Forward Transconductance	$V_{DS} = 10V, I_{D} = 200mA$	g _{fs}	100			mS		
Diode Forward Voltage	$I_S = 300 \text{mA}, V_{GS} = 0 \text{V}$	V_{SD}		0.9	1.2	V		
Dynamic ^b								
Total Gate Charge	$V_{DS} = 10V, I_D = 250mA,$ $V_{GS} = 4.5V$	Q_g		0.4		nC		
Input Capacitance	$V_{DS} = 25V, V_{GS} = 0V,$	C _{iss}		7.32		pF		
Output Capacitance		C _{oss}		3.42				
Reverse Transfer Capacitance	f = 1.0MHz	C _{rss}		7.63				
Switching ^c								
Turn-On Delay Time	$V_{DD} = 30V, R_{G} = 10\Omega$	t _{d(on)}		25		0		
Turn-Off Delay Time	$I_D = 100 \text{mA}, V_{GEN} = 10 \text{V},$	t _{d(off)}		35		nS		

Notes:

- a. pulse test: PW ≤300µS, duty cycle ≤2% b. For DESIGN AID ONLY, not subject to production testing.
- b. Switching time is essentially independent of operating temperature.



Switching Test Circuit

Switchin Waveforms

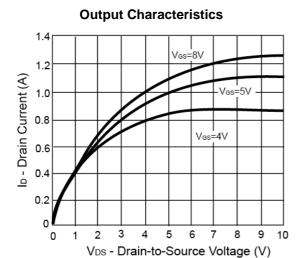
2/6 Version: B12



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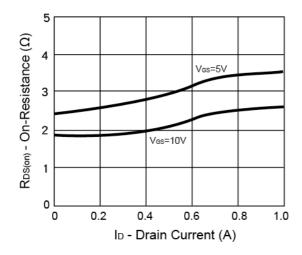


Electrical Characteristics Curve (Ta = 25°C, unless otherwise noted)



1.4 1.2 (V) tues 0.8 0.8 0.6 0.0 0.2

On-Resistance vs. Drain Current



Forward Transfer Admittance vs. Drain Current

5

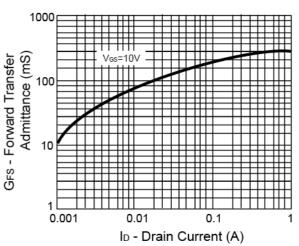
V_{GS} - Gate-to-Source Voltage (V)

6 7 8 9 10

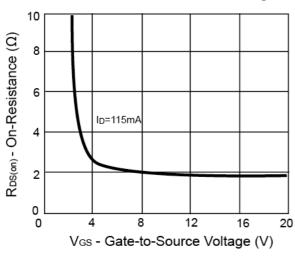
0

0

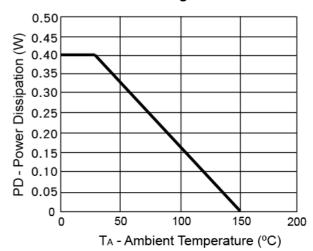
2 3 4



On-Resistance vs. Gate-Source Voltage



Power Derating Curve



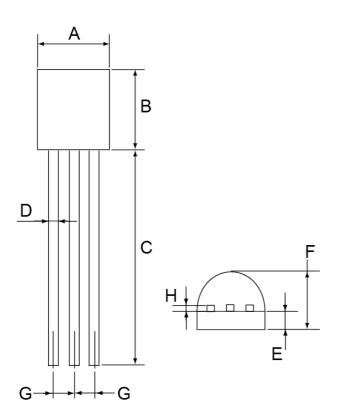
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TO-92 Mechanical Drawing



TO-92 DIMENSION								
DIM	MILLIMETERS		INCHES					
	MIN	MAX	MIN	MAX				
Α	4.30	4.70	0.169	0.185				
В	4.30	4.70	0.169	0.185				
С	13.53 (typ)		0.532 (typ)					
D	0.39	0.49	0.015	0.019				
Е	1.18	1.28	0.046	0.050				
F	3.30	3.70	0.130	0.146				
G	1.27	1.31	0.050	0.051				
Н	0.33	0.43	0.013	0.017				

Marking Diagram



Y = Year Code

M = Month Code

(A=Jan, B=Feb, C=Mar, D=Apl, E=May, F=Jun, G=Jul, H=Aug,

I=Sep, J=Oct, K=Nov, L=Dec)

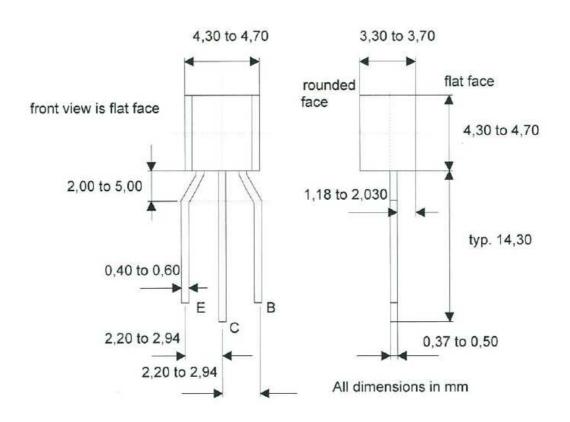
L = Lot Code

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TSM2N7000K 60V N-Channel MOSFET

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